ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33Ω	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	15	mA
				20	
I_H	I_T=500mA		MAX.	10	mA
dV/dt	V_D=400V Gate Open T_j=110		MIN.	50	V/μs
(dV/dt)c	(dI/dt)c=5A/ms, T_j=110		MIN.	2	V/μs
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=15A t_p=380μs	T_j=25	1.6	V
V_{TO}	Threshold voltage	T_j=125	0.8	V
R_D	Dynamic resistance	T_j=125	41	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	/W
$R_{th(j-a)}$	junction to ambient (AC)	100	/W

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

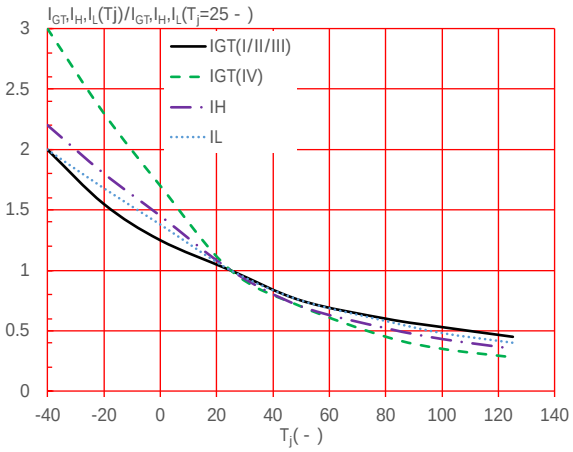

FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

DELIVERY MODE